Lars Samuelson

List of Publications by Year
in descending order

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551 papers	32,244 citations	3515 90 h-index	6113 159 g-index
556 all docs	556 docs citations	556 times ranked	15631 citing authors

#	Article	IF	Citations
1	Quantum Confinement Suppressing Electronic Heat Flow below the Wiedemannâ€“Franz Law. Nano Letters, 2022, 22, 630-635.	4.5	3
2	Quasiparticle Trapping at Vortices Producing Josephson Supercurrent Enhancement. Physical Review Letters, 2022, 128, .	2.9	3
3	Optical-Beam-Induced Current in InAs/InP Nanowires for Hot-Carrier Photovoltaics. ACS Applied Energy Materials, 2022, 5, 7728-7734.	2.5	3
4	From nanoLEDs to the realization of RGB-emitting microLEDs. Semiconductors and Semimetals, 2021, 106, 223-251.	0.4	7
5	From InGaN pyramids to micro-LEDs characterized by cathodoluminescence. Nano Express, 2021, 2, 014006.	1.2	4
6	Semiconductor nanowire array for transparent photovoltaic applications. Applied Physics Letters, 2021, 118, 191107.	1.5	9
7	Aerotaxy: gas-phase epitaxy of quasi 1D nanostructures. Nanotechnology, 2021, 32, 025605.	1.3	11
8	Influence of Contacts and Applied Voltage on a Structure of a Single GaN Nanowire. Applied Sciences (Switzerland), 2021, 11, 9419.	1.3	0
9	Template-assisted vapourâ€“liquidâ€“solid growth of InP nanowires on (001) InP and Si substrates. Nanoscale, 2020, 12, 888-894.	2.8	7
10	Optimization of GaN Nanowires Reformation Process by Metalorganic Chemical Vapor Deposition for Deviceâ€Quality GaN Templates. Physica Status Solidi (B): Basic Research, 2020, 257, 1900581.	0.7	5
11	Dislocationâ€Free and Atomically Flat GaN Hexagonal Microprisms for Device Applications. Small, 2020, 16, 1907364.	5.2	10
12	Hot-carrier separation in heterostructure nanowires observed by electron-beam induced current. Nanotechnology, 2020, 31, 394004.	1.3	10
13	Realization of Ultrahigh Quality InGaN Platelets to be Used as Relaxed Templates for Red Micro-LEDs. ACS Applied Materials & Interfaces, 2020, 12, 17845-17851.	4.0	24
14	Embedded sacrificial AlAs segments in GaAs nanowires for substrate reuse. Nanotechnology, 2020, 31, 204002.	1.3	8
15	Nanowire Solar Cells: A New Radiation Hard PV Technology for Space Applications. IEEE Journal of Photovoltaics, 2020, 10, 502-507.	1.5	15
16	Hot-Carrier Extraction in Nanowire-Nanoantenna Photovoltaic Devices. Nano Letters, 2020, 20, 4064-4072.	4.5	21
17	Evidence of half-integer Shapiro steps originated from nonsinusoidal current phase relation in a short ballistic InAs nanowire Josephson junction. Physical Review Research, 2020, 2, .	1.3	13
18	Irradiation Experiments on High Efficiency Nanowire Solar Cells Including Tilted Incidence Angle. , 2020, , .		0

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19	Local defect-enhanced anodic oxidation of reformed GaN nanowires. Physical Review Materials, 2020, 4, .	0.9	0
20	Optical microprism cavities based on dislocation-free GaN. Applied Physics Letters, 2020, 117, 231107.	1.5	0
21	Synthesis and Applications of IIIâ€“V Nanowires. Chemical Reviews, 2019, 119, 9170-9220.	23.0	208
22	Revealing misfit dislocations in InAs_xP_{1â^'x}-InP coreâ€“shell nanowires by x-ray diffraction. Nanotechnology, 2019, 30, 505703.	1.3	10
23	Radiation Tolerant Nanowire Array Solar Cells. ACS Nano, 2019, 13, 12860-12869.	7.3	27
24	Dominant nonlocal superconducting proximity effect due to electron-electron interaction in a ballistic double nanowire. Science Advances, 2019, 5, eaaw2194.	4.7	26
25	InGaN Platelets: Synthesis and Applications toward Green and Red Light-Emitting Diodes. Nano Letters, 2019, 19, 2832-2839.	4.5	34
26	Nanoprobe-Enabled Electron Beam Induced Current Measurements on III-V Nanowire-Based Solar Cells. , 2019, , .		1
27	High Responsivity of InP/InAsP Nanowire Array Broadband Photodetectors Enhanced by Optical Gating. Nano Letters, 2019, 19, 8424-8430.	4.5	13
28	In situ observation of synthesized nanoparticles in ultra-dilute aerosols via X-ray scattering. Nano Research, 2019, 12, 25-31.	5.8	9
29	Nanowire photodetectors with embedded quantum heterostructures for infrared detection. Infrared Physics and Technology, 2019, 96, 209-212.	1.3	6
30	Surface smoothing and native oxide suppression on Zn doped aerotaxy GaAs nanowires. Journal of Applied Physics, 2019, 125, 025303.	1.1	9
31	Surface and dislocation investigation of planar GaN formed by crystal reformation of nanowire arrays. Physical Review Materials, 2019, 3, .	0.9	7
32	Observation of dominant non-local superconducting proximity effect due to electron-electron interaction in a ballistic double nanowire. , 2019, , .		0
33	Towards Nanowire Tandem Junction Solar Cells on Silicon. IEEE Journal of Photovoltaics, 2018, 8, 733-740.	1.5	53
34	n-type doping and morphology of GaAs nanowires in Aerotaxy. Nanotechnology, 2018, 29, 285601.	1.3	15
35	High In-content InGaN nano-pyramids: Tuning crystal homogeneity by optimized nucleation of GaN seeds. Journal of Applied Physics, 2018, 123, .	1.1	25
36	Temperature dependent electronic band structure of wurtzite GaAs nanowires. Nanoscale, 2018, 10, 1481-1486.	2.8	16

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37	Self-Seeded Axio-Radial InAsâ€"InAs_{1â€"x}P_x Nanowire Heterostructures beyond â€œCommonâ€•VLS Growth. Nano Letters, 2018, 18, 144-151.	4.5	15
38	Intersubband Quantum Disc-in-Nanowire Photodetectors with Normal-Incidence Response in the Long-Wavelength Infrared. Nano Letters, 2018, 18, 365-372.	4.5	34
39	Self-assembled InN quantum dots on side facets of GaN nanowires. Journal of Applied Physics, 2018, 123, .	1.1	14
40	Understanding InP Nanowire Array Solar Cell Performance by Nanoprobe-Enabled Single Nanowire Measurements. Nano Letters, 2018, 18, 3038-3046.	4.5	69
41	Structural Changes in a Single GaN Nanowire under Applied Voltage Bias. Nano Letters, 2018, 18, 5446-5452.	4.5	14
42	Electron Tomography Reveals the Droplet Covered Surface Structure of Nanowires Grown by Aerotaxy. Small, 2018, 14, e1801285.	5.2	5
43	Lattice Tilt Mapping using Full Field Diffraction X-Ray Microscopy at ID01 ESRF. Microscopy and Microanalysis, 2018, 24, 128-129.	0.2	2
44	Using Ultrathin Parylene Films as an Organic Gate Insulator in Nanowire Field-Effect Transistors. Nano Letters, 2018, 18, 4431-4439.	4.5	11
45	Bias-dependent spectral tuning in InP nanowire-based photodetectors. Nanotechnology, 2017, 28, 114006.	1.3	10
46	X-ray Bragg Ptychography on a Single InGaN/GaN Coreâ€"Shell Nanowire. ACS Nano, 2017, 11, 6605-6611.	7.3	43
47	Room-temperature InP/InAsP Quantum Discs-in-Nanowire Infrared Photodetectors. Nano Letters, 2017, 17, 3356-3362.	4.5	36
48	Optimization of Current Injection in AlGaInP Coreâˆ'Shell Nanowire Light-Emitting Diodes. Nano Letters, 2017, 17, 3599-3606.	4.5	15
49	Radial tunnel diodes based on InP/InGaAs core-shell nanowires. Applied Physics Letters, 2017, 110, .	1.5	7
50	Defect-induced infrared electroluminescence from radial GaInP/AlGaInP quantum well nanowire array light- emitting diodes. Nanotechnology, 2017, 28, 485205.	1.3	6
51	InP/InAsP Nanowire-Based Spatially Separate Absorption and Multiplication Avalanche Photodetectors. ACS Photonics, 2017, 4, 2693-2698.	3.2	27
52	Simplifying Nanowire Hall Effect Characterization by Using a Three-Probe Device Design. Nano Letters, 2017, 17, 1121-1126.	4.5	7
53	Gate tunable parallel double quantum dots in InAs double-nanowire devices. Applied Physics Letters, 2017, 111, .	1.5	11
54	GaAsP Nanowire Solar Cell Development Towards Nanowire/Si Tandem Applications. , 2017, , .		0

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55	Nanowire-Based Visible Light Emitters, Present Status and Outlook. Semiconductors and Semimetals, 2016, 94, 227-271.	0.4	35
56	Performance of GaAs Nanowire Array Solar Cells for Varying Incidence Angles. IEEE Journal of Photovoltaics, 2016, 6, 1502-1508.	1.5	18
57	GaAsP Nanowires Grown by Aerotaxy. Nano Letters, 2016, 16, 5701-5707.	4.5	36
58	Recombination dynamics in aerotaxy-grown Zn-doped GaAs nanowires. Nanotechnology, 2016, 27, 455704.	1.3	16
59	InP nanowire p-type doping via Zinc indiffusion. Journal of Crystal Growth, 2016, 451, 18-26.	0.7	5
60	Designed Quasi-1D Potential Structures Realized in Compositionally Graded InAs_{1â€“x}P_x Nanowires. Nano Letters, 2016, 16, 1017-1021.	4.5	8
61	Wurtzite GaAs Quantum Wires: One-Dimensional Subband Formation. Nano Letters, 2016, 16, 2774-2780.	4.5	23
62	Radial Nanowire Light-Emitting Diodes in the (Al_xGa_{1â€“x})_yIn_{1â€“y}P Material System. Nano Letters, 2016, 16, 656-662.	4.5	37
63	A GaAs Nanowire Array Solar Cell With 15.3% Efficiency at 1 Sun. IEEE Journal of Photovoltaics, 2016, 6, 185-190.	1.5	280
64	Comparing Hall Effect and Field Effect Measurements on the Same Single Nanowire. Nano Letters, 2016, 16, 205-211.	4.5	35
65	The optical absorption in zincblende and wurtzite GaP nanowire polytypes. , 2015, , .		0
66	Transport studies of electron-hole and spin-orbit interaction in GaSb/InAsSb core-shell nanowire quantum dots. Physical Review B, 2015, 91, .	1.1	22
67	Strain mapping in an InGaN/GaN nanowire using a nano-focused x-ray beam. Applied Physics Letters, 2015, 107, .	1.5	21
68	Dislocation related droop in InGaN/GaN light emitting diodes investigated via cathodoluminescence. Applied Physics Letters, 2015, 107, .	1.5	39
69	A GaAs nanowire array solar cell with 15.3% efficiency at 1 sun. , 2015, , .		5
70	Nanofocused x-ray beams applied for mapping strain in core-shell nanowires. , 2015, , .		7
71	Selective etching of InP in InAs/InP nanowires resulting in 11 nm nanogaps. , 2015, , .		0
72	Doping GaP Coreâ€“Shell Nanowire pnâ€Junctions: A Study by Offâ€Axis Electron Holography. Small, 2015, 11, 2687-2695.	5.2	22

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73	Zn-doping of GaAs nanowires grown by Aerotaxy. Journal of Crystal Growth, 2015, 414, 181-186.	0.7	28
74	A Comparative Study of Absorption in Vertically and Laterally Oriented InP Coreâ€“Shell Nanowire Photovoltaic Devices. Nano Letters, 2015, 15, 1809-1814.	4.5	57
75	Study of carrier concentration in single InP nanowires by luminescence and Hall measurements. Nanotechnology, 2015, 26, 045705.	1.3	38
76	Structural Properties of Wurtzite InPâ€“InGaAs Nanowire Coreâ€“Shell Heterostructures. Nano Letters, 2015, 15, 2462-2467.	4.5	31
77	Fast Strain Mapping of Nanowire Light-Emitting Diodes Using Nanofocused X-ray Beams. ACS Nano, 2015, 9, 6978-6984.	7.3	25
78	Measurement of strain in InGaN/GaN nanowires and nanopyramids. Journal of Applied Crystallography, 2015, 48, 344-349.	1.9	18
79	In Situ Characterization of Nanowire Dimensions and Growth Dynamics by Optical Reflectance. Nano Letters, 2015, 15, 3597-3602.	4.5	53
80	Confinement in Thickness-Controlled GaAs Polytype Nanodots. Nano Letters, 2015, 15, 2652-2656.	4.5	62
81	InAs Nanowire Transistors with Multiple, Independent Wrap-Gate Segments. Nano Letters, 2015, 15, 2836-2843.	4.5	36
82	IIIâ€“V Nanowire Synthesis by Use of Electrodeposited Gold Particles. Nano Letters, 2015, 15, 134-138.	4.5	22
83	Magnetoresistance in Mn ion-implanted GaAs:Zn nanowires. Applied Physics Letters, 2014, 104, 153112.	1.5	8
84	Nanoscale polymer electrolytes: Fabrication and applications using nanowire transistors. , 2014, , .		0
85	Nanowire-based LEDs and Photovoltaics. , 2014, , .		0
86	Tunable absorption resonances in the ultraviolet for InP nanowire arrays. Optics Express, 2014, 22, 29204.	1.7	22
87	Bulk-like transverse electron mobility in an array of heavily<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math>-doped InP nanowires probed by terahertz spectroscopy. Physical Review B, 2014, 90, .	1.1	24
88	Observation of type-II recombination in single wurtzite/zinc-blende GaAs heterojunction nanowires. Physical Review B, 2014, 89, .	1.1	60
89	Enhanced sputtering and incorporation of Mn in implanted GaAs and ZnO nanowires. Journal Physics D: Applied Physics, 2014, 47, 394003.	1.3	24
90	Formation of nanogaps in InAs nanowires by selectively etching embedded InP segments. Nanotechnology, 2014, 25, 465306.	1.3	10

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91	Semiconductor nanostructures enabled by aerosol technology. Frontiers of Physics, 2014, 9, 398-418.	2.4	19
92	Synthesis of Doped InP Coreâ€"Shell Nanowires Evaluated Using Hall Effect Measurements. Nano Letters, 2014, 14, 749-753.	4.5	30
93	Absorption of light in InP nanowire arrays. Nano Research, 2014, 7, 816-823.	5.8	85
94	Strong Schottky barrier reduction at Au-catalyst/GaAs-nanowire interfaces by electric dipole formation and Fermi-level unpinning. Nature Communications, 2014, 5, 3221.	5.8	54
95	InP/InGaAs core/shell nanowire tunnel diodes for radial tunnel field effect transistor and multi-junction solar cell applications. , 2014, , .		0
96	Electron-Beam Patterning of Polymer Electrolyte Films To Make Multiple Nanoscale Gates for Nanowire Transistors. Nano Letters, 2014, 14, 94-100.	4.5	27
97	Crystal Phase-Dependent Nanophotonic Resonances in InAs Nanowire Arrays. Nano Letters, 2014, 14, 5650-5655.	4.5	26
98	Electrical properties of GaSb/InAsSb core/shell nanowires. Nanotechnology, 2014, 25, 425201.	1.3	32
99	Nanowire LEDs and Solar Cells. , 2014, , .		0
100	Straight and kinked InAs nanowire growth observed in situ by transmission electron microscopy. Nano Research, 2014, 7, 1188-1194.	5.8	19
101	Growth and characterization of wurtzite GaP nanowires with control over axial and radial growth by use of HCl in-situ etching. Journal of Crystal Growth, 2014, 386, 47-51.	0.7	32
102	GaAs/AlGaAs heterostructure nanowires studied by cathodoluminescence. Nano Research, 2014, 7, 473-490.	5.8	34
103	Study of photocurrent generation in InP nanowire-based p+-i-n+ photodetectors. Nano Research, 2014, 7, 544-552.	5.8	37
104	InN quantum dots on GaN nanowires grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 421-424.	0.8	4
105	Microarray Analysis Reveals Moderate Gene Expression Changes in Cortical Neural Stem Cells Cultured on Nanowire Arrays. Journal of Nanoscience and Nanotechnology, 2014, 14, 4880-4885.	0.9	15
106	Large-energy-shift photon upconversion in degenerately doped InP nanowires by direct excitation into the electron gas. Nano Research, 2013, 6, 752-757.	5.8	6
107	Fluorescent Nanowire Heterostructures as a Versatile Tool for Biology Applications. Nano Letters, 2013, 13, 4728-4732.	4.5	43
108	Photoluminescence study of Zn-doped wurtzite InP core-shell nanowires. Applied Physics Letters, 2013, 102, 032105.	1.5	3

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109	Magnetic Polarons and Large Negative Magnetoresistance in GaAs Nanowires Implanted with Mn Ions. Nano Letters, 2013, 13, 5079-5084.	4.5	26
110	Semiconductor-Oxide Heterostructured Nanowires Using Postgrowth Oxidation. Nano Letters, 2013, 13, 5961-5966.	4.5	8
111	Conductance Enhancement of InAs/InP Heterostructure Nanowires by Surface Functionalization with Oligo(phenylene vinylene)s. ACS Nano, 2013, 7, 4111-4118.	7.3	16
112	III-V and III-nitride nanowires for LED applications. , 2013, , .		1
113	InP Nanowire Array Solar Cells Achieving 13.8% Efficiency by Exceeding the Ray Optics Limit. Science, 2013, 339, 1057-1060.	6.0	1,093
114	Nanowire-Based Electrode for Acute In Vivo Neural Recordings in the Brain. PLoS ONE, 2013, 8, e56673.	1.1	73
115	Nanoscale energy converters. , 2013, , .		0
116	Optical Far-Field Method with Subwavelength Accuracy for the Determination of Nanostructure Dimensions in Large-Area Samples. Nano Letters, 2013, 13, 2662-2667.	4.5	15
117	Photoluminescence study of as-grown vertically standing wurtzite InP nanowire ensembles. Nanotechnology, 2013, 24, 115706.	1.3	15
118	Fibroblasts Cultured on Nanowires Exhibit Low Motility, Impaired Cell Division, and DNA Damage. Small, 2013, 9, 4006-4016.	5.2	94
119	Currentâ€"Voltage Characterization of Individual As-Grown Nanowires Using a Scanning Tunneling Microscope. Nano Letters, 2013, 13, 5182-5189.	4.5	16
120	MOVPE-grown InAs/AlAs0.16Sb0.84/InAs and InAs/AlAs0.16Sb0.84/GaSb heterostructures. Journal of Crystal Growth, 2013, 374, 43-48.	0.7	2
121	Control and understanding of kink formation in InAsâ€"InP heterostructure nanowires. Nanotechnology, 2013, 24, 345601.	1.3	14
122	Reflection measurements to reveal the absorption in nanowire arrays. Optics Letters, 2013, 38, 1449.	1.7	11
123	Transparently wrap-gated semiconductor nanowire arrays for studies of gate-controlled photoluminescence. , 2013, , .		1
124	Optical characterization of InAs quantum wells and dots grown radially on wurtzite InP nanowires. Nanotechnology, 2013, 24, 225203.	1.3	11
125	Lineshape of the thermopower of quantum dots. New Journal of Physics, 2012, 14, 033041.	1.2	60
126	Phonon Transport and Thermoelectricity in Defect-Engineered InAs Nanowires. Materials Research Society Symposia Proceedings, 2012, 1404, 36.	0.1	6

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127	Single GaInP nanowire p-i-n junctions near the direct to indirect bandgap crossover point. Applied Physics Letters, 2012, 100, 251103.	1.5	13
128	Spatially resolved Hall effect measurement in a single semiconductor nanowire. Nature Nanotechnology, 2012, 7, 718-722.	15.6	158
129	Continuous gas-phase synthesis of nanowires with tunable properties. Nature, 2012, 492, 90-94.	13.7	156
130	Electron Trapping in InP Nanowire FETs with Stacking Faults. Nano Letters, 2012, 12, 151-155.	4.5	102
131	Realizing Lateral Wrap-Gated Nanowire FETs: Controlling Gate Length with Chemistry Rather than Lithography. Nano Letters, 2012, 12, 1-6.	4.5	83
132	Colorful InAs Nanowire Arrays: From Strong to Weak Absorption with Geometrical Tuning. Nano Letters, 2012, 12, 1990-1995.	4.5	90
133	Hopping Conduction in Mn Ion-Implanted GaAs Nanowires. Nano Letters, 2012, 12, 4838-4842.	4.5	39
134	Cell Type Dependent Effects of Nanowire Density on Cell Cultures. Biophysical Journal, 2012, 102, 585a.	0.2	0
135	Tunnel Field-Effect Transistors Based on InP-GaAs Heterostructure Nanowires. ACS Nano, 2012, 6, 3109-3113.	7.3	89
136	Surface Chemistry, Structure, and Electronic Properties from Microns to the Atomic Scale of Axially Doped Semiconductor Nanowires. ACS Nano, 2012, 6, 9679-9689.	7.3	37
137	Electrical and optical properties of InP nanowire ensemble p⁺â€“iâ€“n⁺photodetectors. Nanotechnology, 2012, 23, 135201.	1.3	31
138	Particle-assisted Ga_xIn_{1â^'x}P nanowire growth for designed bandgap structures. Nanotechnology, 2012, 23, 245601.	1.3	48
139	Thermoelectric Characterization of Electronic Properties of GaMnAs Nanowires. Journal of Nanotechnology, 2012, 2012, 1-5.	1.5	10
140	Vertical oxide nanotubes connected by subsurface microchannels. Nano Research, 2012, 5, 190-198.	5.8	35
141	Creating dynamic nanowire devices using wrapped gates. , 2011, , .		0
142	Gate-Induced Fermi Level Tuning in InP Nanowires at Efficiency Close to the Thermal Limit. Nano Letters, 2011, 11, 1127-1130.	4.5	19
143	Probing the Wurtzite Conduction Band Structure Using State Filling in Highly Doped InP Nanowires. Nano Letters, 2011, 11, 2286-2290.	4.5	66
144	Scanning gate imaging of quantum dots in 1D ultra-thin InAs/InP nanowires. Nanotechnology, 2011, 22, 185201.	1.3	19

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145	A New Route toward Semiconductor Nanospintronics: Highly Mn-Doped GaAs Nanowires Realized by Ion-Implantation under Dynamic Annealing Conditions. Nano Letters, 2011, 11, 3935-3940.	4.5	47
146	Thermal conductivity of indium arsenide nanowires with wurtzite and zinc blende phases. Physical Review B, 2011, 83, .	1.1	96
147	Axial InP Nanowire Tandem Junction Grown on a Silicon Substrate. Nano Letters, 2011, 11, 2028-2031.	4.5	114
148	Growth of doped InAsyP1â^'y nanowires with InP shells. Journal of Crystal Growth, 2011, 331, 8-14.	0.7	27
149	Self-seeded, position-controlled InAs nanowire growth on Si: A growth parameter study. Journal of Crystal Growth, 2011, 334, 51-56.	0.7	41
150	GaAs-based Nanowires Studied by Low-Temperature Cathodoluminescence. Journal of Physics: Conference Series, 2011, 326, 012042.	0.3	2
151	Dual-gate induced InP nanowire diode. , 2011, , .		0
152	Nanowires With Promise for Photovoltaics. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 1050-1061.	1.9	123
153	InSb Nanowire Field-Effect Transistors and Quantum-Dot Devices. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 907-914.	1.9	34
154	Dynamics of extremely anisotropic etching of InP nanowires by HCl. Chemical Physics Letters, 2011, 502, 222-224.	1.2	16
155	Valence band splitting in wurtzite InP nanowires observed by photoluminescence and photoluminescence excitation spectroscopy. Nano Research, 2011, 4, 159-163.	5.8	41
156	Photoluminescence of Mgâ€doped mâ€plane GaN grown by MOCVD on bulk GaN substrates. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1532-1534.	0.8	6
157	Diffusion length measurements in axial and radial heterostructured nanowires using cathodoluminescence. Journal of Crystal Growth, 2011, 315, 138-142.	0.7	24
158	Fabrication and characterization of AlP-GaP core-shell nanowires. Journal of Crystal Growth, 2011, 324, 290-295.	0.7	6
159	Doping profile of InP nanowires directly imaged by photoemission electron microscopy. Applied Physics Letters, 2011, 99, 233113.	1.5	16
160	Thermal resistance of a nanoscale point contact to an indium arsenide nanowire. Applied Physics Letters, 2011, 99, 063110.	1.5	15
161	Signatures of Wigner localization in epitaxially grown nanowires. Physical Review B, 2011, 83, .	1.1	28
162	InAs quantum dots and quantum wells grown on stacking-fault controlled InP nanowires with wurtzite crystal structure. Applied Physics Letters, 2011, 99, 131915.	1.5	30

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163	Degenerate p-doping of InP nanowires for large area tunnel diodes. Applied Physics Letters, 2011, 99, .	1.5	28
164	GaSb nanowire single-hole transistor. Applied Physics Letters, 2011, 99, 262104.	1.5	34
165	Photoluminescence of Mg-doped m -plane GaN grown by MOCVD on bulk GaN substrates. Proceedings of SPIE, 2011, , .	0.8	2
166	Toward 3D Integration of 1D Conductors: Junctions of InAs Nanowires. Journal of Nanomaterials, 2011, 2011, 1-5.	1.5	1
167	Low-temperature cathodoluminescence studies of GaAs nanowires in the SEM. Journal of Physics: Conference Series, 2010, 241, 012085.	0.3	2
168	In situ etching for total control over axial and radial nanowire growth. Nano Research, 2010, 3, 264-270.	5.8	135
169	III-V Nanowiresâ€"Extending a Narrowing Road. Proceedings of the IEEE, 2010, 98, 2047-2060.	16.4	85
170	Growth and segregation of GaAsâ€"AlxIn1â^'xP core-shell nanowires. Journal of Crystal Growth, 2010, 312, 1755-1760.	0.7	39
171	Time-resolved photoluminescence investigations on HfO₂-capped InP nanowires. Nanotechnology, 2010, 21, 105711.	1.3	18
172	Correlation-Induced Conductance Suppression at Level Degeneracy in a Quantum Dot. Physical Review Letters, 2010, 104, 186804.	2.9	52
173	Control of IIIâ€"V nanowire crystal structure by growth parameter tuning. Semiconductor Science and Technology, 2010, 25, 024009.	1.0	219
174	Integration, gap formation, and sharpening of III-V heterostructure nanowires by selective etching. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 21-26.	0.6	12
175	Comparative friction measurements of InAs nanowires on three substrates. Journal of Applied Physics, 2010, 108, 094307.	1.1	12
176	Determination of diffusion lengths in nanowires using cathodoluminescence. Applied Physics Letters, 2010, 97, .	1.5	33
177	Semiconductor nanowires as a bottom-up approach to realize nanoelectronic and nanophotonic devices. , 2010, , .		0
178	Bias-controlled friction of InAs nanowires on a silicon nitride layer studied by atomic force microscopy. Physical Review B, 2010, 82, .	1.1	16
179	Branched nanotrees with immobilized acetylcholine esterase for nanobiosensor applications. Nanotechnology, 2010, 21, 055102.	1.3	10
180	Charge pumping in InAs nanowires by surface acoustic waves. Semiconductor Science and Technology, 2010, 25, 024013.	1.0	8

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181	Changes in Contact Angle of Seed Particle Correlated with Increased Zincblende Formation in Doped InP Nanowires. Nano Letters, 2010, 10, 4807-4812.	4.5	83
182	Crystal Phase Engineering in Single InAs Nanowires. Nano Letters, 2010, 10, 3494-3499.	4.5	234
183	Diameter Dependence of the Wurtziteâˆ'Zinc Blende Transition in InAs Nanowires. Journal of Physical Chemistry C, 2010, 114, 3837-3842.	1.5	129
184	New Flexible Toolbox for Nanomechanical Measurements with Extreme Precision and at Very High Frequencies. Nano Letters, 2010, 10, 3893-3898.	4.5	8
185	Probing Strain in Bent Semiconductor Nanowires with Raman Spectroscopy. Nano Letters, 2010, 10, 1280-1286.	4.5	85
186	Fifteen-Piconewton Force Detection from Neural Growth Cones Using Nanowire Arrays. Nano Letters, 2010, 10, 782-787.	4.5	109
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